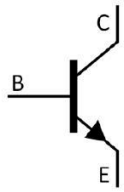
Silicon NPN transistor in a TO-126F Plastic Package.

Complement to BD140.

Medium power linear and switching applications.

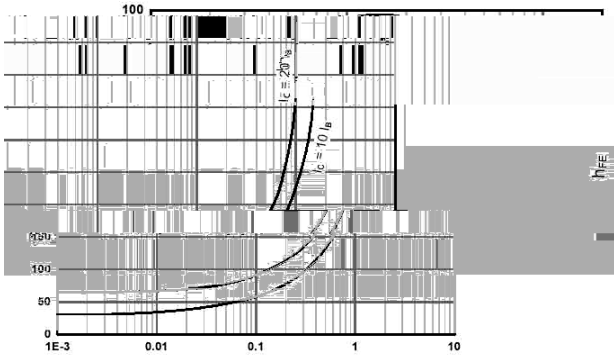


PIN1 Emitter PIN 2 Collector PIN 3 Base

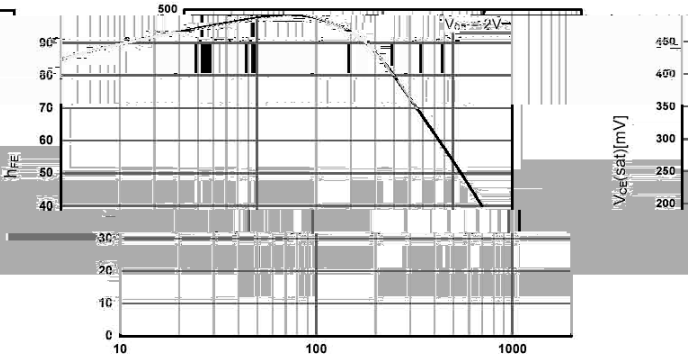
h_{FE} Classifications Symbol	6	10	16	25
h_{FE} Range	40～100	63～160	100～250	160～400

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous	I_{CP}	3.0	A
Base Current – Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	1.25	W
Collector Power Dissipation	P_C(Tc=25)	12.5	W
Junction Temperature	T_j	150	EBC 55 2

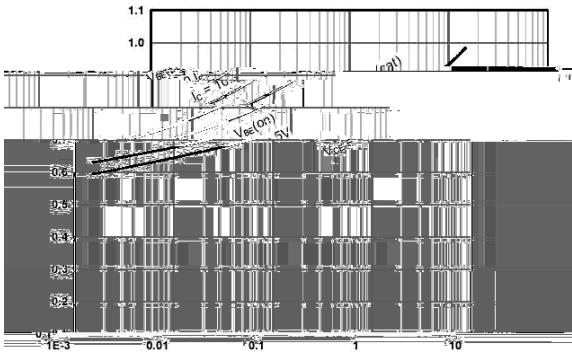
h_{FE} — I_C



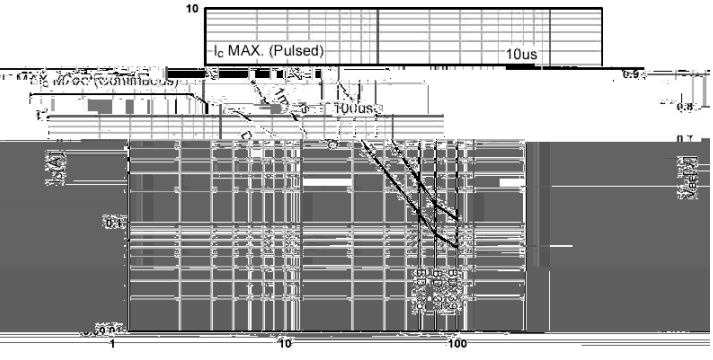
$V_{CE}(sat)$ — I_C



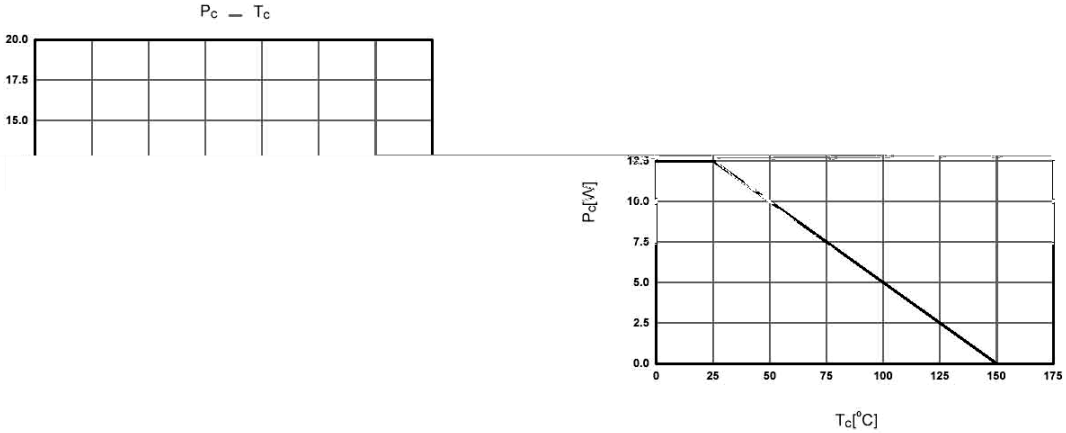
V_{BE} — I_C



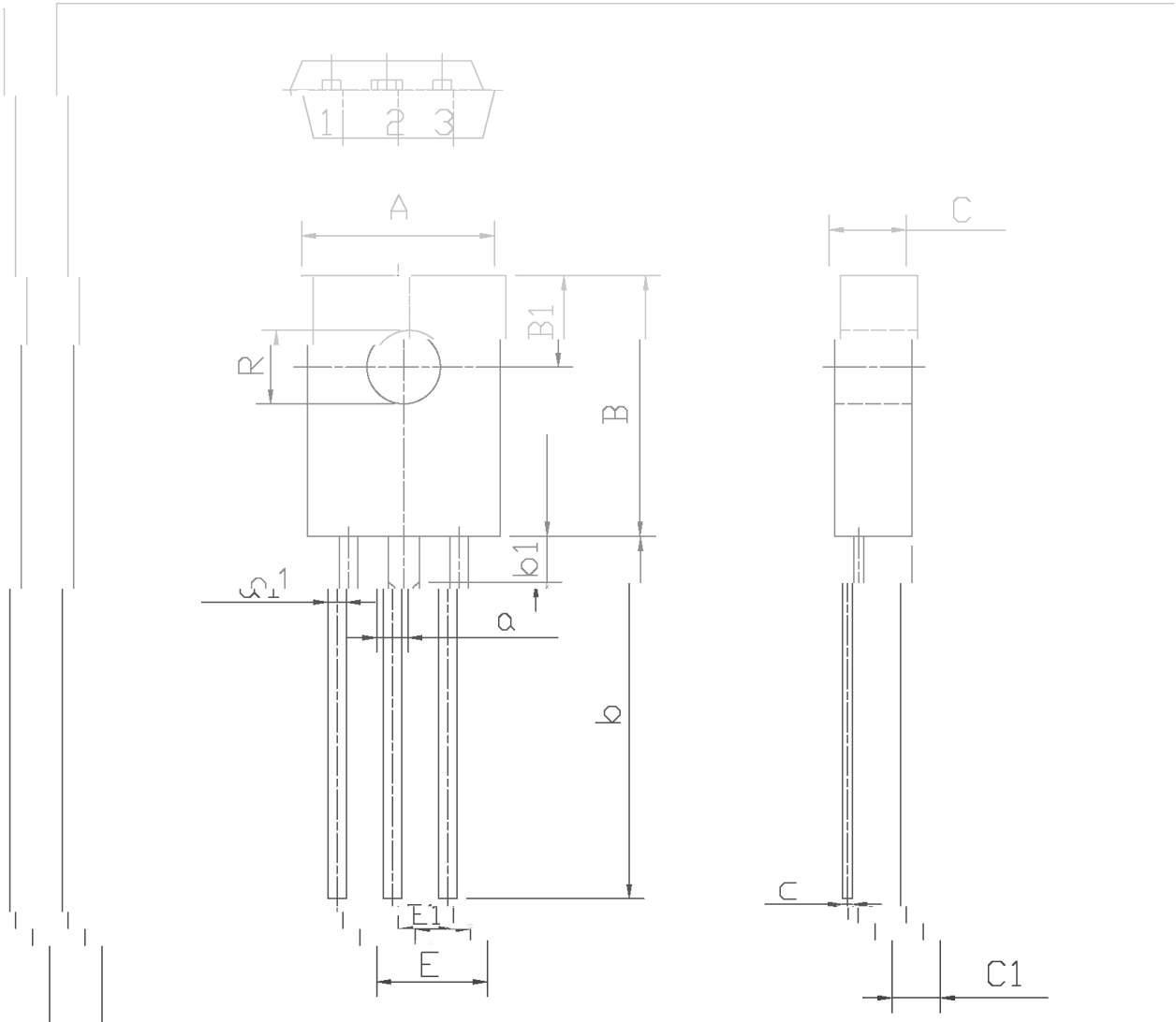
I_C — V_{CE}



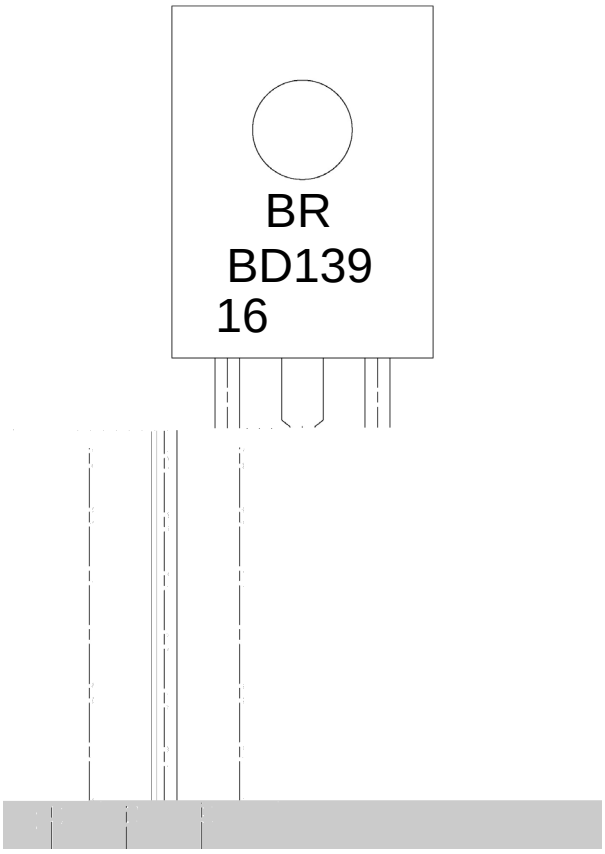
P_C — T_C



单位：mm

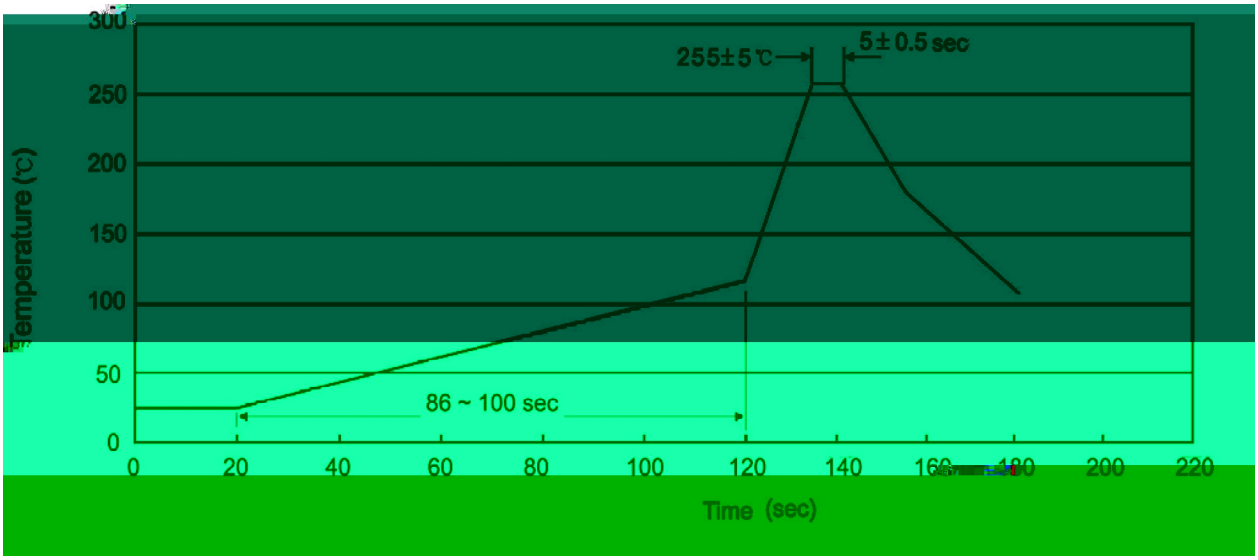


Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	7.8	8.2	a1	0.66	0.86
B	10.8	11.2	E	4.4	4.8
B1	3.8	4.2	C	3.1	3.3
R	2.95	3.15	C1	1.9	2.1
b	14	16	c	0.3	0.6
b1	1.9		a	1.27	
E1	2.1	2.5			



Note:

BR:	Company Code
BD139:	Product Type.
16:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.



					Note:
1		25	150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255	5	5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3					